IN THE CLAIMS:

1.   (Currently Amended) A memory module, comprising:

a fast non-volatile random access memory, responsive to a command/data signal provided by a processor, ~~for providing~~ configured to provide a permanent storage of information before said command/data signal is provided, ~~for executing~~ configured to execute a command comprised in said command/data signal using said permanently stored information for providing a direct communication between said fast non-volatile random access memory and the processor; and

a double data interface configured to communicate with said processor,

wherein said memory module and said processor are parts of an electronic device.

2.   (Currently Amended) The memory module of claim 1, wherein ~~an~~ said double data interface is between the processor and the fast non-volatile random access memory and is a double data rate type.

3.   (Currently Amended) The memory module of claim 1, wherein the fast non-volatile random access memory ~~provides~~ is configured to provide a temporal storage of data comprised in said command/data signal.

4.   (Currently Amended) The memory module of claim 3, wherein said fast non-volatile random access memory comprises:

an information storage area configured to permanently store ~~for the permanent storage of~~ said information; and

a temporal data storage area configured to temporally store ~~for the temporal storage of~~ said data.

5.   (Currently Amended) The memory module of claim 4, wherein said fast non-volatile random access memory further comprises:

at least one register ~~for setting~~configured to set operating parameters of the fast non-volatile random access memory or ~~protecting~~to protect said data or said information during said execution.

6.   (Currently Amended) The memory module of claim 5, wherein said operating parameters comprise ~~one or more~~at least one of of: ~~a)~~timings for a particular frequency, and ~~b)~~frequency ranges with a corresponding core voltage range.

7.   (Currently Amended) The memory module of claim 5, wherein ~~said~~protecting said data or said information during said execution comprises a write protection.

8.   (Previously Presented) The memory module of claim 1, wherein said information comprises an application program for operating said electronic device.

9.   (Currently Amended) The memory module of claim 1, further comprising:

a mass memory, ~~for providing~~ configured to provide further information in response to a command/information signal; and

an application-specific integration circuit, responsive to said command/data signal, configured to provide ~~for providing~~ said command/information signal.

10.   (Original) The memory module of claim 9, wherein said further information is provided to said fast non-volatile random access memory.

11.   (Currently Amended) The memory module of claim 10, wherein said fast non-volatile random access memory ~~executes~~ is configured to execute a further command comprised in said command/data signal using said further information.

12.   (Previously Presented) The memory module of claim 9, wherein an interface between the application-specific integration circuit and the fast non-volatile random access memory is a double data rate type.

13.   (Previously Presented) The memory module of claim 9, wherein a non-volatile random access memory-integrated circuit package contains the application-specific integration circuit, the mass memory and the fast non-volatile random access memory, or said non-volatile random access memory-integrated circuit package contains the application-specific integration circuit and the fast non-volatile random access memory, or said non-volatile random access memory-integrated circuit package contains the mass memory and the fast non-volatile random access memory.

14.   (Currently Amended) The memory module of claim 9, further comprising:
       a dynamic random access memory, responsive to a command/data signal, ~~for providing~~configured to provide a storage of said further information, wherein said further information is provided or partially provided to the dynamic random access memory by the mass memory in response to said command/information signal.

15.   (Previously Presented) The memory module of claim 14, wherein a non-volatile random access memory-integrated circuit

package contains the application-specific integration circuit, the mass memory, the fast non-volatile random access memory and the dynamic random access memory, or said non-volatile random access memory-integrated circuit package contains the application-specific integration circuit and the fast non-volatile random access memory, or said non-volatile random access memory-integrated circuit package contains the mass memory, the dynamic random access memory and the fast non-volatile random access memory.

16.   (Currently Amended) The memory module of claim 14, wherein said dynamic random access memory ~~executes~~ is configured to execute a still further command comprised in said command/data signal using said further information.

17.   (Currently Amended) The memory module of claim 14, wherein ~~an~~ said electronic device comprises:

       a removable mass memory, configured to provide~~for providing~~, in response to a further command/information signal provided by the application-specific integration circuit, still further information to the fast non-volatile random access memory, or to the dynamic random access memory, or to both the fast non-volatile random access memory and to the dynamic random access memory.

18.   (Currently Amended) The memory module of claim 17, wherein said fast non-volatile random access memory or the dynamic random access memory or both the fast non-volatile random access memory and the dynamic random access memory ~~execute~~ are configured to execute a further command or a still further command or both the further command and the still further command comprised in said

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command/data signal using said further information or said still further information or both the further information and the still further information.

19. (Original) The memory module of claim 1, wherein said fast non-volatile random access memory is a magneto-resistive random access memory, a ferroelectric random access memory, or an Ovonics memory type.

20. (Currently Amended) An electronic device, comprising
a processor, ~~for providing~~ configured to provide a command/data signal and optionally for providing an overall operation control of said electronic device; ~~and~~
a fast non-volatile random access memory, responsive to the command/data signal, configured to provide ~~for providing~~ a permanent storage of information before said command/data signal is provided, ~~for executing~~ configured to execute a command comprised in said command/data signal using said stored information; and
a double data interface configured to communicate with said processor.

21. (Currently Amended) The electronic device of claim 20, further comprising:
a power and reset block, ~~for resetting~~ configured to reset said processor and ~~for resetting~~ said fast non-volatile random access memory.

22. (Currently Amended) The ~~electronic device~~ memory module of claim ~~20~~ 1, wherein said electronic device is a portable electronic device, a mobile electronic device or a mobile phone.

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Claims 23-32 are cancelled

33.   (Currently Amended) An apparatus, comprising:

means for uninterrupted storage, responsive to a command/data signal provided by a processor, configured to provide a permanent storage of information before said command/data signal is provided, configured to execute a command contained in said command/data signal using said permanently stored information for providing a direct communication between said means for uninterrupted storage and the processor; and

means for doubling data rate configured to communicate with said processor.

~~means for responding to a command/data signal provided by a processor, for providing a permanent storage of information before receiving said command/data signal, for executing a command comprised in said command/data signal using said permanently stored information to provide a direct communication between said means and the processor.~~

34.   (Currently Amended) The apparatus of claim 33, wherein said means for uninterrupted storage is a fast non-volatile random access memory and said means for doubling data rate is a double data interface.~~wherein said apparatus is a memory module~~.